SN74CB3T3383 10-BIT FET BUS-EXCHANGE SWITCH 2.5-V/3.3-V LOW-VOLTAGE BUS SWITCH WITH 5-V-TOLERANT LEVEL SHIFTER

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- Output Voltage Translation Tracks V_{CC}
- Supports Mixed-Mode Signal Operation On All Data I/O Ports
 - 5-V Input Down To 3.3-V Output Level Shift With 3.3-V V_{CC}
 - 5-V/3.3-V Input Down To 2.5-V Output Level Shift With 2.5-V V_{CC}
- 5-V-Tolerant I/Os With Device Powered Up or Powered Down
- Bidirectional Data Flow, With Near-Zero Propagation Delay
- Low ON-State Resistance (r_{on})
 Characteristics (r_{on} = 5 Ω Typical)
- Low Input/Output Capacitance Minimizes Loading (C_{io(OFF)} = 8 pF Typical)
- Data and Control Inputs Provide Undershoot Clamp Diodes
- Low Power Consumption (I_{CC} = 20 μA Max)

- V_{CC} Operating Range From 2.3 V to 3.6 V
- Data I/Os Support 0- to 5-V Signaling Levels (0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V, 3.3 V, 5 V)
- Control Inputs Can Be Driven by TTL or 5-V/3.3-V CMOS Outputs
- I_{off} Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- ESD Performance Tested Per JESD 22
 - 2000-V Human-Body Model (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)
- Supports Digital Applications: Level Translation, Memory Interleaving, Bus Isolation
- Ideal for Low-Power Portable Equipment

DBQ, DGV, DW, OR PW PACKAGE (TOP VIEW)

_		_	
1	\bigcup_{2}	լի	V_{CC}
2	23	3 🛭	5B2
3	22	2 🏻	5A2
4	2	þ	5A1
5	20		5B1
6	19	9	4B2
7	18	3 🛮	4A2
8	17	7	4A1
9	16	3	4B1
10	15	5 🛮	3B2
11	14	1	3A2
12	13	3	ВХ
	3 4 5 6 7 8 9 10	2 23 3 22 4 21 5 20 6 19 7 18 8 17 9 16 10 15	3 22 4 21 5 20 6 19 7 18 8 17 9 16 10 15

description/ordering information

ORDERING INFORMATION

TA	PACKAGE	<u></u> †	TOP-SIDE MARKING	
	2010 1011	Tube	SN74CB3T3383DW	ODOTOGO
	SOIC – DW	Tape and reel	SN74CB3T3383DWR	CB3T3383
40°C to 95°C	SSOP (QSOP) – DBQ	Tape and reel	SN74CB3T3383DBQR	CB3T3383
–40°C to 85°C	TOOOD DW	Tube	SN74CB3T3383PW	1/2222
	TSSOP – PW	Tape and reel	SN74CB3T3383PWR	KS383
	TVSOP - DGV	Tape and reel	SN74CB3T3383DGVR	KS383

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

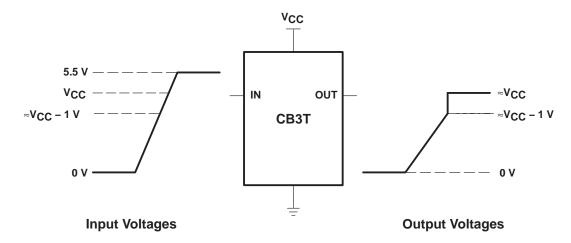


2.5-V/3.3-V LOW-VOLTAGE BUS SWITCH WITH 5-V-TOLERANT LEVEL SHIFTER

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description/ordering information (continued)

The SN74CB3T3383 is a high-speed TTL-compatible FET bus-exchange switch with low ON-state resistance (r_{on}) , allowing for minimal propagation delay. The device fully supports mixed-mode signal operation on all data I/O ports by providing voltage translation that tracks V_{CC} . The SN74CB3T3383 supports systems using 5-V TTL, 3.3-V LVTTL, and 2.5-V CMOS switching standards, as well as user-defined switching levels (see Figure 1).



NOTE A: If the input high voltage (V_{IH}) level is greater than or equal to V_{CC} – 1 V, and less than or equal to 5.5 V, then the output high voltage (V_{OH}) level will be equal to approximately the V_{CC} voltage level.

Figure 1. Typical DC Voltage Translation Characteristics

The SN74CB3T3383 is organized as a 10-bit bus switch or as a 5-bit bus-exchange with enable ($\overline{\text{BE}}$) input. When used as a 5-bit bus-exchange, the device provides data exchanging between four signal ports. When $\overline{\text{BE}}$ is low, the bus-exchange switch is ON, and the select input (BX) controls the data path. When $\overline{\text{BE}}$ is high, the bus-exchange switch is OFF, and a high-impedance state exists between the A and B ports.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} feature ensures that damaging current will not backflow through the device when it is powered down. The device has isolation during power off.

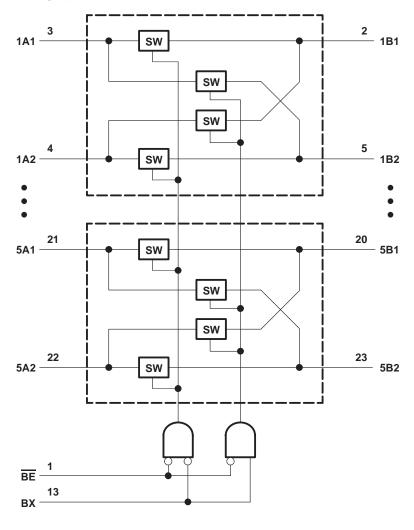
To ensure the high-impedance state during power up or power down, \overline{BE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.



FUNCTION TABLE (each 5-bit switch)

INP	UTS	INPUTS/0	OUTPUTS	FUNCTION
BE	вх	A1	A2	FUNCTION
L	L	B1	B2	A1 port = B1 port A2 port = B2 port
L	Н	B2	B1	A1 port = B2 port A2 port = B1 port
Н	Х	Z	Z	Disconnect

logic diagram (positive logic)

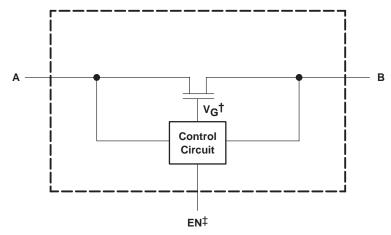




2.5-V/3.3-V LOW-VOLTAGE BUS SWITCH WITH 5-V-TOLERANT LEVEL SHIFTER

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simplified schematic, each FET switch (SW)



[†] Gate Voltage (V_G) is approximately equal to $V_{CC} + V_T$ when the switch is ON and $V_I > V_{CC} + V_T$.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)§

Supply voltage range, V _{CC} (see Note 1)		–0.5 V to 7 V
Control input voltage range, V _{IN} (see Notes 1 and	2)	-0.5~V to $7~V$
Switch I/O voltage range, V _{I/O} (see Notes 1, 2, and	d 3)	-0.5~V to $7~V$
Control input clamp current, I _{IK} (V _{IN} < 0)		–50 mA
I/O port clamp current, $I_{I/OK}$ ($V_{I/O} < 0$)		–50 mA
ON-state switch current, I _{I/O} (see Note 4)		±128 mA
Continuous current through V _{CC} or GND terminals	\$	±100 mA
Package thermal impedance, θ _{JA} (see Note 5): DE	BQ package	61°C/W
DO	GV package	86°C/W
DV	W package	46°C/W
PV	W package	88°C/W
Storage temperature range, T _{stq}		65°C to 150°C

[§] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltages are with respect to ground unless otherwise specified.
 - 2. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
 - 3. V_I and V_O are used to denote specific conditions for $V_{I/O}$.
 - 4. I_I and I_O are used to denote specific conditions for I_{I/O}.
 - 5. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions (see Note 6)

			MIN	MAX	UNIT
VCC	Supply voltage		2.3	3.6	V
.,		V _{CC} = 2.3 V to 2.7 V	1.7	5.5	.,
V_{IH}	High-level control input voltage	V _{CC} = 2.7 V to 3.6 V	2	5.5	V
.,	Low-level control input voltage $ \frac{V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}}{V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}} $.,
V_{IL}					V
V _{I/O}	Data input/output voltage		0	5.5	V
TA	Operating free-air temperature		-40	85	°C

NOTE 6: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



[‡] EN is the internal enable signal applied to the switch.

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PAR	AMETER	TEST CONDITION	S	MIN	TYP	MAX	UNIT	
VIK		V _{CC} = 3 V, I _I = -18 mA				-1.2	V	
Vон		See Figures 3 and 4						
I _{IN} ‡	Control inputs	$V_{CC} = 3.6 \text{ V},$ $V_{IN}^{\ddagger} = 3.6 \text{ V to } 5.5 \text{ V or GND}$				±10	μΑ	
		V _{CC} = 3.6 V,	$V_I = V_{CC} - 0.7 \text{ V to } 5.5 \text{ V}$			±20		
lį		Switch ON,	$V_I = 0.7 \text{ V to } V_{CC} - 0.7 \text{ V}$			-40	μΑ	
		$V_{IN} = V_{CC}$ or GND	V _I = 0 to 0.7 V			±5		
l _{OZ} §	$V_{CC} = 3.6 \text{ V},$ $V_{O} = 0 \text{ to } 5.5 \text{ V},$ $V_{I} = 0,$ Switch OFF, $V_{IN} = V_{CC} \text{ or GND}$					±10	μΑ	
l _{off}		$V_{CC} = 0,$ $V_{O} = 0 \text{ to } 5.5 \text{ V},$ $V_{I} = 0,$				10	μΑ	
		$V_{CC} = 3.6 \text{ V},$ $I_{I/O} = 0,$ $V_{I} = V_{CC} \text{ or GND}$				20	•	
ICC		Switch ON or OFF, V _{IN} = V _{CC} or GND	V _I = 5.5 V			20	μΑ	
ΔICC¶	Control inputs	$V_{CC} = 3 \text{ V to } 3.6 \text{ V,}$ One input at $V_{CC} - 0.6 \text{ V,}$ Other inputs at V_{CC} or GND				300	μΑ	
C _{in}	Control inputs	$V_{CC} = 3.3 \text{ V},$ $V_{IN} = V_{CC} \text{ or GND}$			4		pF	
C _{io(OFF)}		$V_{CC} = 3.3 \text{ V},$ $V_{I/O} = 5.5 \text{ V}, 3.3 \text{ V}, \text{ or GND},$ Switch OFF, $V_{IN} = V_{CC} \text{ or GND}$			8		pF	
C:-(ON)		V _{CC} = 3.3 V, Switch ON.	V _{I/O} = 5.5 V or 3.3 V		7		pF	
C _{io(ON)}		V _{IN} = V _{CC} or GND	$V_{I/O} = GND$	21			þr	
		V _{CC} = 2.3 V, TYP at V _{CC} = 2.5 V,	I _O = 24 mA		5	9		
ron#		V _I = 0	I _O = 16 mA		5	9	9 8	
OH		V _{CC} = 3 V,	I _O = 64 mA		5	8		
		V _I = 0		5	8			

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$ (unless otherwise noted), $T_A = 25^{\circ}\text{C}$. ‡ V_{IN} and I_{IN} refer to control inputs. V_{I} , V_{O} , I_{I} , and I_{O} refer to data pins. § For I/O ports, the parameter I_{OZ} includes the input leakage current.

This is the increase in supply current for each input that is at the specified TTL voltage level, rather than V_{CC} or GND.

[#] Measured by the voltage drop between A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

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switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

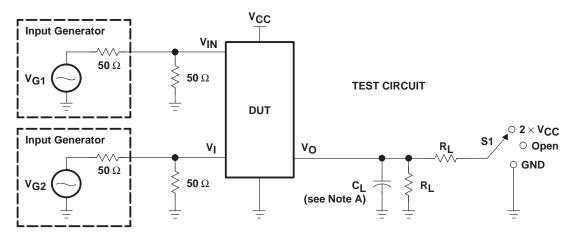
PARAMETER	FROM	TO	V _{CC} =		V _{CC} =	UNIT	
	(INPUT)	(OUTPUT)	MIN	MAX	MIN	MAX	
_{tpd} †	A or B	B or A		0.15		0.25	
tpd(s)	BX	A or B	1	15	1	10	ns
t _{en}	BE	A or B	1	13.5	1	9	ns
^t dis	BE	A or B	1	7	1	8.5	ns

[†]The propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

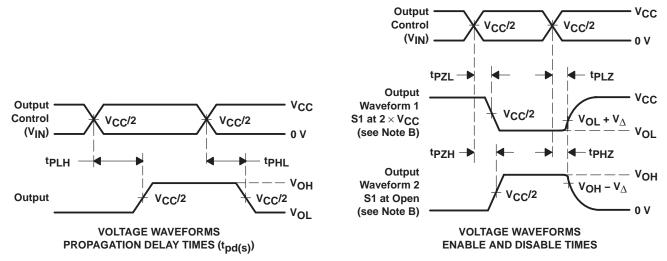


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PARAMETER MEASUREMENT INFORMATION



TEST	VCC	S1	RL	VI	CL	${f v}_{\Delta}$
tpd(s)	2.5 V \pm 0.2 V	Open	500 Ω	3.6 V or GND	30 pF	
ρα(ο)	3.3 V \pm 0.3 V	Open	500 Ω	5.5 V or GND	50 pF	
tpl z/tpzl	2.5 V \pm 0.2 V	2×V _{CC}	500 Ω	GND	30 pF	0.15 V
'PLZ''PZL	3.3 V \pm 0.3 V	2×V _{CC}	500 Ω	GND	50 pF	0.3 V
t/t	2.5 V \pm 0.2 V	Open	500 Ω	3.6 V	30 pF	0.15 V
tPHZ/tPZH	3.3 V \pm 0.3 V	Open	500 Ω	5.5 V	50 pF	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50 \Omega$, $t_f \leq 2.5 \text{ ns.}$
- D. The outputs are measured one at a time, with one transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd(s). The tpd propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).
- H. All parameters and waveforms are not applicable to all devices.

Figure 2. Test Circuit and Voltage Waveforms



TYPICAL CHARACTERISTICS

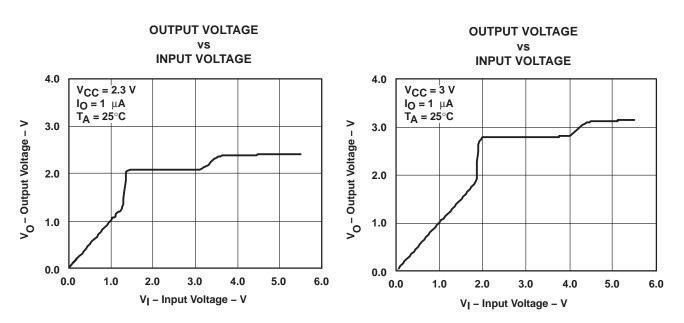
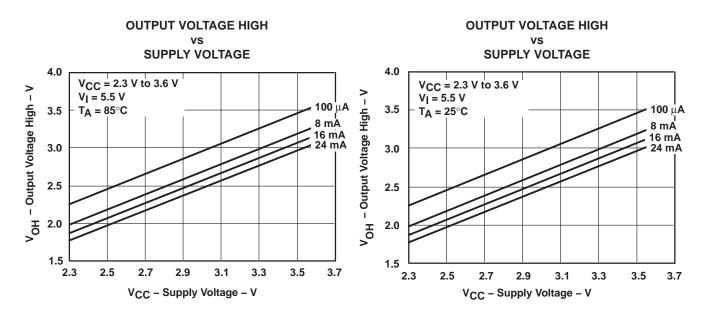


Figure 3. Data Output Voltage vs Data Input Voltage



TYPICAL CHARACTERISTICS (continued)



OUTPUT VOLTAGE HIGH vs

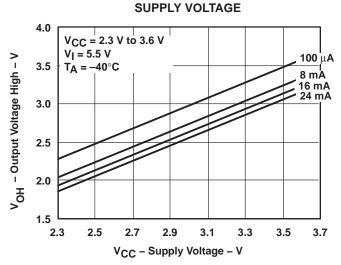


Figure 4. V_{OH} Values

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
SN74CB3T3383DGVR	ACTIVE	TVSOP	DGV	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS383	Samples
SN74CB3T3383DWR	ACTIVE	SOIC	DW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3T3383	Samples
SN74CB3T3383PW	ACTIVE	TSSOP	PW	24	60	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS383	Samples
SN74CB3T3383PWR	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS383	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74CB3T3383DGVR	TVSOP	DGV	24	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CB3T3383DWR	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1
SN74CB3T3383PWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1

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*All dimensions are nominal

Device	Package Type Package Drawing		Pins SPQ		Length (mm)	Width (mm)	Height (mm)	
SN74CB3T3383DGVR	TVSOP	DGV	24	2000	367.0	367.0	35.0	
SN74CB3T3383DWR	SOIC	DW	24	2000	350.0	350.0	43.0	
SN74CB3T3383PWR	TSSOP	PW	24	2000	356.0	356.0	35.0	

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

	Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
ı	SN74CB3T3383PW	PW	TSSOP	24	60	530	10.2	3600	3.5

DW (R-PDSO-G24)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AD.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



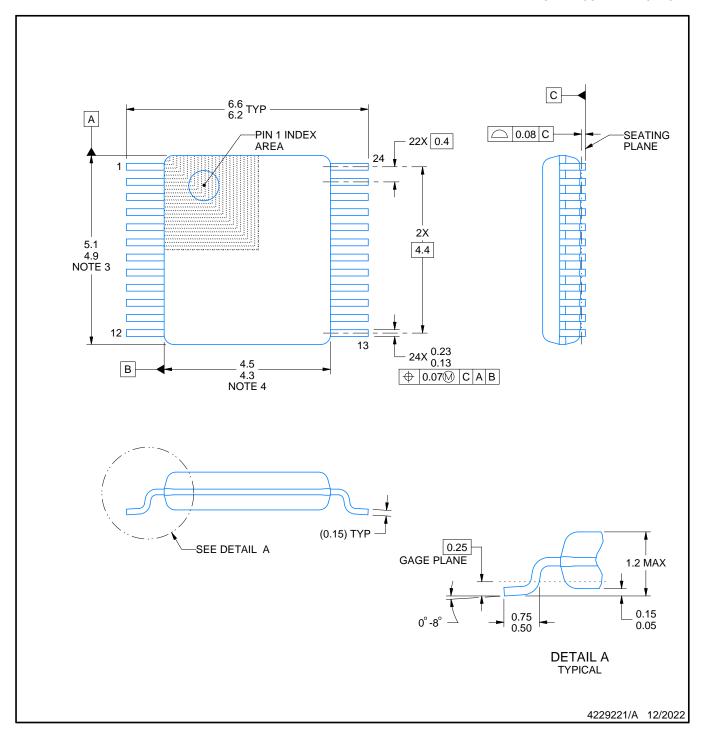


NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







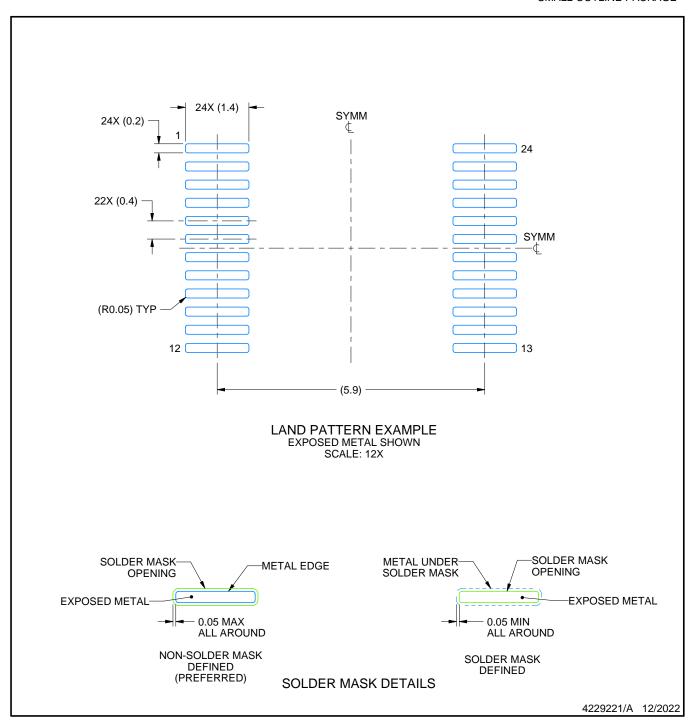
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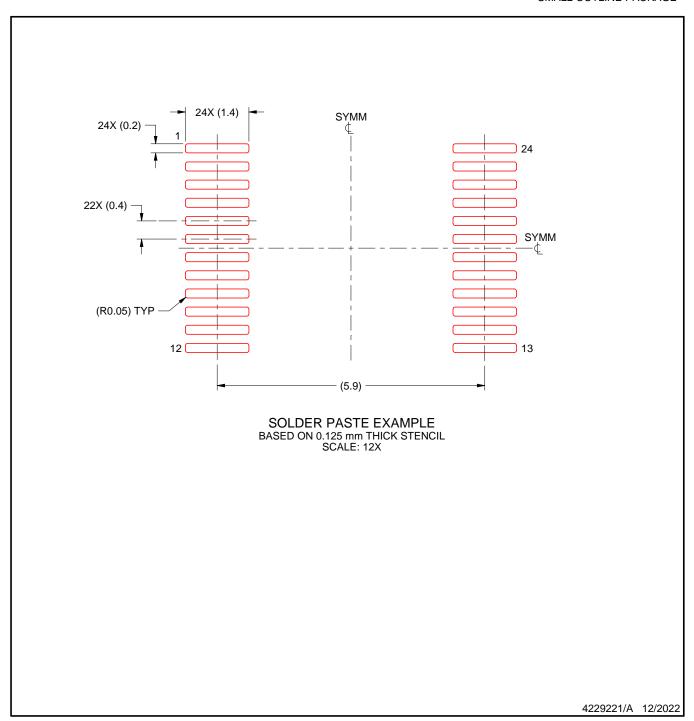


NOTES: (continued)

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NOTES: (continued)

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